

# MA3X198

## Silicon epitaxial planar type

For general purpose

### ■ Features

- Two elements contained in one package, allowing high-density mounting
- Soft recovery characteristic ( $t_{rr} = 100$  ns)
- Can be connected in series

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	40	V
Repetitive peak reverse voltage	$V_{RRM}$	40	V
Average forward current	Single	$I_{F(AV)}$	100
	Series		75
Repetitive peak forward current	Single	$I_{FRM}$	225
	Series		170
Non-repetitive peak forward surge current*	Single	$I_{FSM}$	500
	Series		325
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

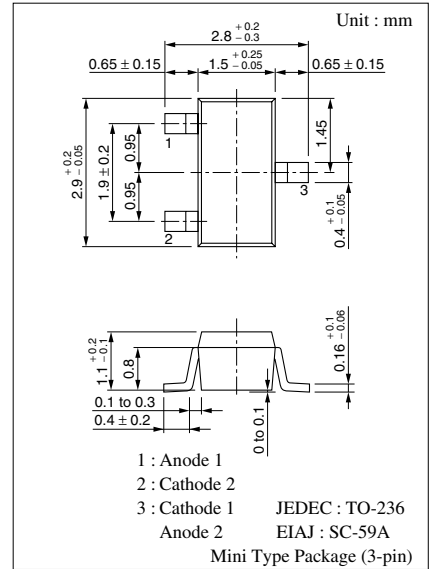
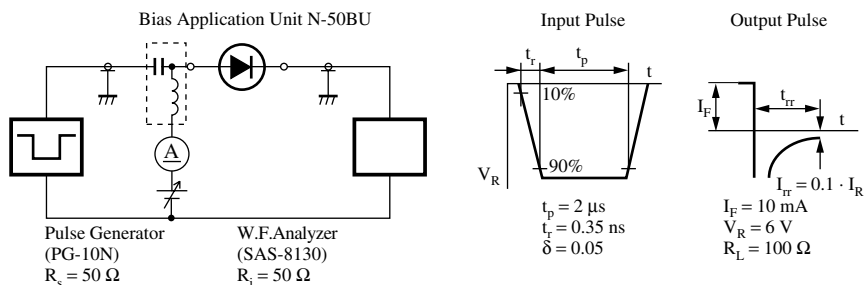
Note) \* :  $t = 1$  s

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 40$ V			10	nA
Forward voltage (DC)	$V_{F1}$	$I_F = 100$ $\mu\text{A}$	0.65		0.72	V
	$V_{F2}$	$I_R = 100$ mA			1.2	V
Terminal capacitance	$C_t$	$V_R = 6$ V, $f = 1$ MHz		1	2	pF
Reverse recovery time*	$t_{rr}$	$I_F = 10$ mA, $V_R = 6$ V $I_{rr} = 0.1 \cdot I_R$ , $R_L = 100$ $\Omega$			100	ns

Note) 1. Rated input/output frequency: 100 MHz

2. \* :  $t_{rr}$  measuring circuit



Marking Symbol: M2F

Internal Connection

